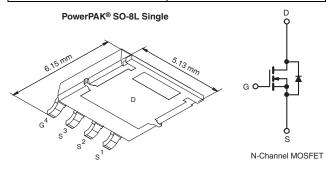


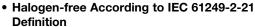
Vishay Siliconix

Automotive N-Channel 40 V (D-S) 175 °C MOSFET

PRODUCT SUMMARY			
V _{DS} (V)	40		
$R_{DS(on)}(\Omega)$ at $V_{GS} = 10 \text{ V}$	0.0045		
$R_{DS(on)}(\Omega)$ at $V_{GS} = 4.5 \text{ V}$	0.0055		
I _D (A)	32		
Configuration	Single		



FEATURES





- TrenchFET® Power MOSFET
- Compliant to RoHS Directive 2002/95/EC
- AEC-Q101 Qualifiedd
- Find out more about Vishay's Automotive Grade Product Requirements at: www.vishay.com/applications

RoHS
HALOGEN FREE

AUTOMOTIVE GRADE

ORDERING INFORMATION	
Package	PowerPAK SO-8L
Lead (Pb)-free and Halogen-free	SQJ412EP-T1-GE3

ABSOLUTE MAXIMUM RATINGS (T _C = 25 °C, unless otherwise noted)					
PARAMETER		SYMBOL	LIMIT	UNIT	
Drain-Source Voltage		V_{DS}	40	V	
Gate-Source Voltage		V_{GS}	± 20	V	
Continuous Drain Current ^a	T _C = 25 °C	1	32		
	T _C = 125 °C	I _D	32		
Continuous Source Current (Diode Conduction) ^a		I _S	32	Α	
Pulsed Drain Current ^b		I _{DM}	128		
Single Pulse Avalanche Current	L = 0.1 mH	I _{AS}	53		
Single Pulse Avalanche Energy	L=0.1 min	E _{AS}	140	mJ	
Maximum Power Dissipation ^b	T _C = 25 °C	D	83	W	
	T _C = 125 °C	P_{D}	27	VV	
Operating Junction and Storage Temperature Range		T _J , T _{stg}	- 55 to + 175	°C	
Soldering Recommendations (Peak Temperature) ^{e, f}			260	C	

THERMAL RESISTANCE RATINGS				
PARAMETER		SYMBOL	LIMIT	UNIT
Junction-to-Ambient	PCB Mount ^c	R _{thJA}	65	°C/W
Junction-to-Case (Drain)		R _{thJC}	1.8	C/VV

Notes

- a. Package limited.
- b. Pulse test; pulse width $\leq 300~\mu s,~duty~cycle \leq 2~\%.$
- c. When mounted on 1" square PCB (FR-4 material).
- d. Parametric verification ongoing.
- e. See Solder Profile (www.vishay.com/ppg?73257). The PowerPAK SO-8L. The end of the lead terminal is exposed copper (not plated) as a result of the singulation process in manufacturing. A solder fillet at the exposed copper tip cannot be guaranteed and is not required to ensure adequate bottom side solder interconnection.
- f. Rework conditions: manual soldering with a soldering iron is not recommended for leadless components.

SQJ412EP

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SPECIFICATIONS ($T_C = 25 ^{\circ}C$,	unless otherw	vise noted)					
PARAMETER	SYMBOL	TES	TEST CONDITIONS		TYP.	MAX.	UNIT
Static					•		
Drain-Source Breakdown Voltage	V _{DS}	$V_{GS} = 0 \text{ V}, I_D = 250 \mu\text{A}$		40	-	-	V
Gate-Source Threshold Voltage	V _{GS(th)}	V _{DS} =	= V _{GS} , I _D = 250 μA	1.5	2.0	2.5	V
Gate-Source Leakage	I _{GSS}	V _{DS} =	$0 \text{ V}, \text{ V}_{GS} = \pm 20 \text{ V}$	-	-	± 100	nA
		$V_{GS} = 0 V$	V _{DS} = 40 V	-	-	1	
Zero Gate Voltage Drain Current	I _{DSS}	$V_{GS} = 0 V$	V _{DS} = 40 V, T _J = 125 °C	-	-	50	μΑ
		$V_{GS} = 0 V$	V _{DS} = 40 V, T _J = 175 °C	-	-	150	•
On-State Drain Currenta	I _{D(on)}	V _{GS} = 10 V	$V_{DS} \ge 5 V$	30	-	-	Α
Drain-Source On-State Resistance ^a		V _{GS} = 10 V	I _D = 10.3 A	-	0.0034	0.0045	
		V _{GS} = 10 V	I _D = 10.3 A, T _J = 125 °C	-	0.0053	0.0070	Ω
	R _{DS(on)}	V _{GS} = 10 V	I _D = 10.3 A, T _J = 175 °C	-	0.0065	0.0085	
		V _{GS} = 4.5 V	I _D = 8.7 A	-	0.0040	0.0055	
Forward Transconductanceb	9 _{fs}	V_{DS}	= 15 V, I _D = 16 A	-	85	-	S
Dynamic ^b					•		
Input Capacitance	C _{iss}		V _{DS} = 20 V, f = 1 MHz	-	4950	5950	pF
Output Capacitance	C _{oss}	$V_{GS} = 0 V$		-	630	760	
Reverse Transfer Capacitance	C _{rss}			-	270	330	
Total Gate Charge ^c	Qg		V _{DS} = 20 V, I _D = 10 A	-	80	120	nC
Gate-Source Charge ^c	Q _{gs}	V _{GS} = 10 V		-	13.1	-	
Gate-Drain Charge ^c	Q _{gd}			-	12.3	-	
Turn-On Delay Time ^c	t _{d(on)}		$V_{DD} = 20 \text{ V, R}_1 = 2.0 \Omega$		45	55	- ns
Rise Time ^c	t _r	V _{DD} =			150	180	
Turn-Off Delay Time ^c	t _{d(off)}	$I_D \cong$ 10 A, $V_{GEN} = 4.5$ V, $R_g = 6$ Ω		-	50	60	
Fall Time ^c	t _f			-	55	70	
Source-Drain Diode Ratings and Char	acteristics ^b	•			•		
Pulsed Current ^a	I _{SM}			-	-	128	Α
Forward Voltage	V _{SD}	I _F = 10 A, V _{GS} = 0 V		-	0.8	1.1	V

Notes

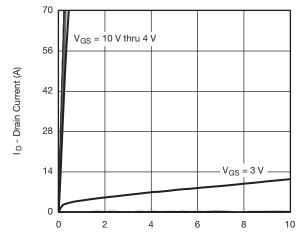
- a. Pulse test; pulse width $\leq 300~\mu s,$ duty cycle $\leq 2~\%.$
- b. Guaranteed by design, not subject to production testing.
- c. Independent of operating temperature.

Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.



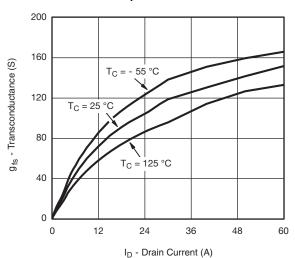


TYPICAL CHARACTERISTICS (T_A = 25 °C, unless otherwise noted)

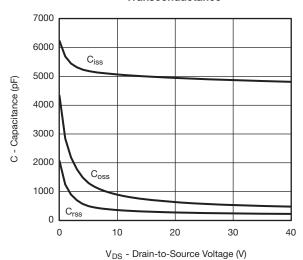


V_{DS} - Drain-to-Source Voltage (V)

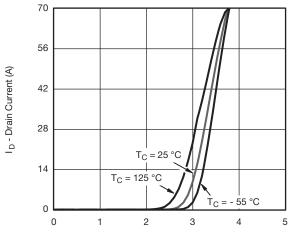
Output Characteristics



Transconductance

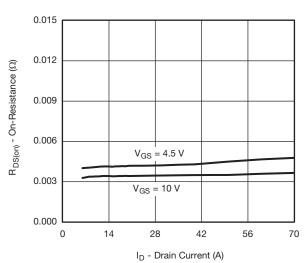


Capacitance

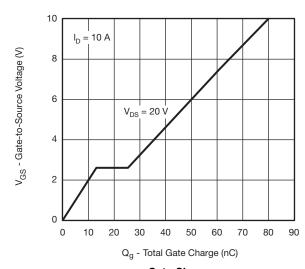


V_{GS} - Gate-to-Source Voltage (V)

Transfer Characteristics



On-Resistance vs. Drain Current

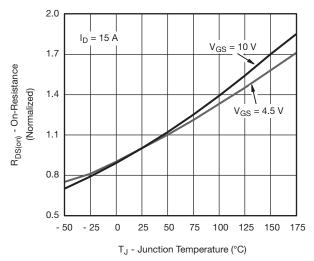


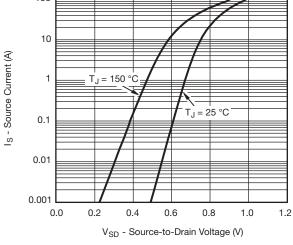
Gate Charge

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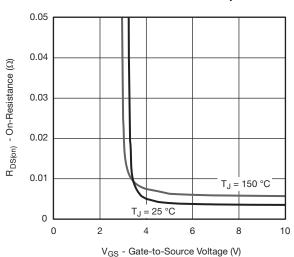


TYPICAL CHARACTERISTICS (T_A = 25 °C, unless otherwise noted)

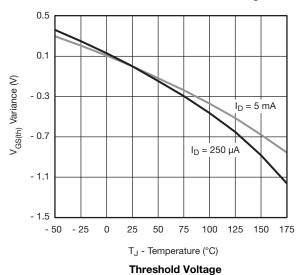




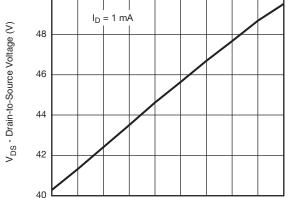
On-Resistance vs. Junction Temperature



Source Drain Diode Forward Voltage



On-Resistance vs. Gate-to-Source Voltage



0 25 50 75 100 125 150 175 T_J - Junction Temperature (°C)

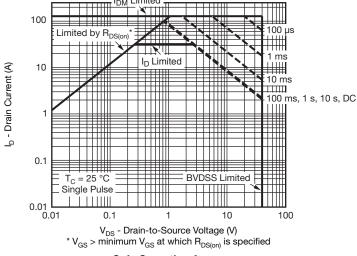
Drain Source Breakdown vs. Junction Temperature

- 50 - 25

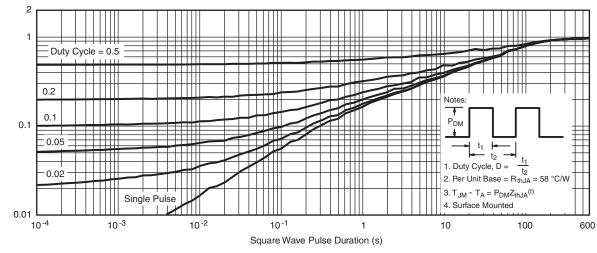


Normalized Effective Transient Thermal Impedance

THERMAL RATINGS (T_A = 25 °C, unless otherwise noted)



Safe Operating Area

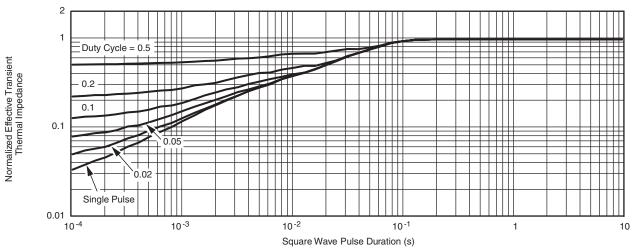


Normalized Thermal Transient Impedance, Junction-to-Ambient

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THERMAL RATINGS (T_A = 25 °C, unless otherwise noted)



Normalized Thermal Transient Impedance, Junction-to-Case

Note

- The characteristics shown in the two graphs
 - Normalized Transient Thermal Impedance Junction-to-Ambient (25 °C)
 - Normalized Transient Thermal Impedance Junction-to-Case (25 °C) are given for general guidelines only to enable the user to get a "ball park" indication of part capabilities. The data are extracted from single pulse transient thermal impedance characteristics which are developed from empirical measurements. The latter is valid for the part mounted on printed circuit board FR4, size 1" x 1" x 0.062", double sided with 2 oz. copper, 100 % on both sides. The part capabilities

can widely vary depending on actual application parameters and operating conditions.

Vishay Siliconix maintains worldwide manufacturing capability. Products may be manufactured at one of several qualified locations. Reliability data for Silicon Technology and Package Reliability represent a composite of all qualified locations. For related documents such as package/tape drawings, part marking, and reliability data, see www.vishay.com/ppg?65935.





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